



Krishna Acharya

Photocurrent Spectroscopy of Semiconductor Thin Films

Application of Pulsed-laser Deposition in
Photosensitive Hetero-pairing of CdS /
Plastic, CdS / Glass, and ZnTe / GaAs

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PREFACE

This book is the result of my graduate work at Bowling Green State University (BGSU), Bowling Green, Ohio, USA, during 2004-09. This work presents photocurrent (PC) spectroscopy of thin-film cadmium sulfide (CdS) on plastic, CdS on glass, and zinc telluride (ZnTe) on gallium arsenide (GaAs) hetero-pairs. All samples have been prepared with pulsed-laser deposition (PLD) and the work is organized into three principal sections as described below.

In the first section, the merger of a transparent plastic substrate with thin-film CdS for photonic application was realized using low-temperature PLD, where low-temperature PLD means the substrates were not externally heated. Although plastic is not considered to be a favored substrate material for semiconductor thin-film formation, the deposited CdS film possessed good adhesion to the plastic substrates and showed a blue-shifted photosensitivity with peak at 2.54 eV. The CdS deposition rate was monitored at different laser fluences and the maximum rate was found at 2.68 J/cm^2 . The visualization of the surface using an atomic force microscope (AFM) revealed its mosaic structure and electron probe microanalysis showed that target composition was maintained in the film. The study of thickness distribution revealed that the film deposition area is significantly increased with increase in laser fluence. The achieved results demonstrate the capability of PLD to form novel heterostructures with appealing and useful technological properties such as plasticity and low weight.

In the second part, APC control via blue light illumination employing thin-film PLD CdS on a glass is introduced. In fact, the APC driven through the CdS film in conjunction with bias was quenched when the sample was additionally illuminated with a blue light emitting diode (LED). It occurred that the quenching magnitude depends on the blue light intensity, chopped light intensity and its energy, and applied electric field. The quenching phenomenon is attributed to the shortening of available APC carriers because of the generation of direct current channels in the film and is described using a straightforward band diagram model.

In the final part of the dissertation, the PC spectra modification of a *n*-GaAs substrate due to the PLD of thin-film ZnTe is presented. The intrinsic and extrinsic room temperature PC spectra of the *n*-GaAs and ZnTe/*n*-GaAs samples were investigated with lock-in technique by employing various optical chopping frequencies and biases. The PC magnitude of the bulk *n*-GaAs was increased with increasing chopper frequency, while PC of the ZnTe/*n*-GaAs sample

showed an increase and decrease with frequency in the lower and higher energy range, respectively. Noteworthy, a frequency independent isosbestic point was observed at the crossover between these two behaviors at 1.88 eV. Additionally, a defect related PC peak at 1.37 eV was observed only for ZnTe/*n*-GaAs sample. The magnitude of the peak-and even its appearance-was found to be sensitively dependent on the sign of bias. This phenomenon caused by PLD created defect states on *n*-GaAs surface referred to “photonic-doping”.

I would like to express my sincere gratitude to my academic advisor Dr. Bruno Ullrich, without whose inspirations, guidance, and support; this work would not be possible. My PhD committee members Dr. Deanne Snavelly, Dr. John Cable, and Dr. Lewis Fulcher are highly acknowledged for their valuable inputs and suggestions in this work. I am indebted to Dr. Artur Erlacher for his help and assistance in the laboratory and many invaluable suggestions and inputs during my graduate work at BGSU. Dr. Chinthaka Liyanage, Dina Atoyan, Dr. Dale Smith from BGSU; Dr. Himal Khatri, Jonathan Skuza,; Dr. Alejandra Lukaszew from University of Toledo; H. Sakai from Hiroshima Kokusai Gakuin University Japan; and K. Mahalingam, F. Meisenkothen from the Air Force Research Laboratory Dayton are highly acknowledged for their help and research collaboration.

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This work is dedicated to my family members, especially, to my wife Shobha, daughter Eliza, and son Kushal for their company, love, and support that always inspired me to succeed.

ABBREVIATION AND ACRONYMS

AES: Auger electron spectroscopy

AFM: Atomic force microscopy

APC: Alternating photocurrent

As: Arsenic

CB: Conduction band

CdS: Cadmium sulfide

CW: Continuous wave

DPC: Direct photocurrent

eV: Electron volt

ETRI: Electronics and telecommunications research institute

Ga: Gallium

GaAs: Gallium arsenide

GaSb: Gallium antimonide

GPB: General purpose interface bus

He-Ne: Helium neon

HOMO: Highest occupied molecular orbital

HRTEM: High resolution transmission electron micrograph

HWE: Hot wall epitaxy

IR: Infrared

I-V: Current versus voltage

LED: Light emitting diode

LUMO: Lowest unoccupied molecular orbital

MBE: Molecular beam epitaxy

meV: Millielectron volt, 10^{-3} electron volt

min.: Minute

MOCVD: Metal-organic chemical vapor deposition

ms: Millisecond, 10^{-3} second

mW: Milliwatt, 10^{-3} W

Nd:YAG: Neodymium doped yttrium aluminum garnet

nm: Nanometer, 10^{-9} meter
ns: Nanosecond, 10^{-9} second
PC: Photocurrent
PET: Polyethylene terephthalate
PL: Photoluminescence
PLD: Pulsed-laser deposition
PR: Photoreflectance
RHEED: Reflection high energy electron diffraction.
S: Sulfur
SEM: Scanning electron microscopy
Si: Silicon
SIMS: Secondary ion mass spectroscopy
SQUID: Superconducting quantum interference device
Subs.: Substrate
Te: Tellurium
TEM: Transmission electron microscopy.
Temp.: Temperature
TGVPD: Temperature gradient vapor phase deposition
TGVTD: Temperature gradient vapor transport deposition
VB: Valance band
XRD: X-ray diffraction
YBCO: Yttrium barium copper oxide
ZnTe: Zinc telluride

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TABLE OF CONTENTS

| | | |
|-------|---|----|
| 1 | BACKGROUND AND MOTIVATION | 1 |
| 1.1 | Outline | 1 |
| 1.2 | General background | 1 |
| 1.3 | Objectives of the research | 3 |
| 2 | INTRODUCTION AND FUNDAMENTALS | 5 |
| 2.1 | Semiconductors | 5 |
| 2.1.1 | Energy bands in semiconductors | 5 |
| 2.1.2 | Doping in semiconductors | 6 |
| 2.2 | Photoconductivity | 7 |
| 2.2.1 | Photocurrent spectroscopy | 9 |
| 2.2.2 | Photocurrent spectrum equation | 9 |
| 2.3 | Pulsed-laser deposition of thin films | 11 |
| 2.3.1 | Mechanism of pulsed-laser deposition | 12 |
| 2.3.2 | Applications of pulsed-laser deposition: an overview | 13 |
| 2.3.3 | Restrictions of PLD | 15 |
| 3 | PULSED-LASER DEPOSITION OF CdS FILMS ON PLASTIC | 16 |
| 3.1 | General introduction | 16 |
| 3.2 | Cadmium sulfide fundamentals | 16 |
| 3.3 | Plastic (polyethylene terephthalate) fundamental | 18 |
| 3.4 | Literature review | 19 |
| 3.4.1 | Pulsed-laser deposition of CdS | 19 |
| 3.4.2 | Pulsed-laser deposition of different materials on the polymer substrate | 19 |
| 3.5 | Experimental setup | 25 |
| 3.5.1 | Laser system | 25 |
| 3.5.2 | Optical system | 25 |
| 3.5.3 | Vacuum system | 25 |
| 3.5.4 | PLD of CdS and deposition rate | 26 |
| 3.6 | Plasma plume investigation | 28 |
| 3.7 | CdS/plastic sample preparation | 29 |

| | | |
|-------|--|----|
| 3.8 | Conclusions | 31 |
| 4 | CdS/PLASTIC CHARACTERIZATION | 32 |
| 4.1 | Surface characterization | 32 |
| 4.2 | Crystallographic properties | 33 |
| 4.3 | Composition of the film | 36 |
| 4.4 | Thickness distribution | 39 |
| 4.4.1 | Thickness distribution measurement setup | 39 |
| 4.4.2 | Thickness distribution of the film | 40 |
| 4.5 | Photocurrent measurement | 41 |
| 4.5.1 | Direct photocurrent measurement setup | 41 |
| 4.5.2 | Photocurrent and transmission spectra of CdS/Plastic | 43 |
| 4.6 | Conclusions | 45 |
| 5 | OPTICAL QUENCHING OF ALTERNATING PHOTOCURRENT IN CdS/GLASS | 46 |
| 5.1 | Introduction | 46 |
| 5.2 | Experimental | 47 |
| 5.3 | Results and discussion | 50 |
| 5.3.1 | Structural and optical properties | 50 |
| 5.3.2 | APC spectra at different chopper frequency and voltages | 52 |
| 5.3.3 | Quenching of alternating responsivity with blue light excitation | 55 |
| 5.3.4 | Explanation of the quenching phenomenon | 58 |
| 5.4 | Conclusions | 59 |
| 6 | PHOTOCURRENT SPECTROSCOPY OF ZnTe/ <i>n</i> -GaAs | 60 |
| 6.1 | Introduction | 60 |
| 6.1.1 | Zinc Telluride | 60 |
| 6.1.2 | Gallium Arsenide | 60 |
| 6.1.3 | ZnTe/GaAs heteropairs | 61 |
| 6.2 | Experimental | 64 |
| 6.2.1 | Device formation | 64 |
| 6.2.2 | <i>I</i> - <i>V</i> characteristics setup | 64 |
| 6.2.3 | Alternating photocurrent measurement setup | 65 |
| 6.3 | Results and discussion | 66 |

| | | |
|-------|---|----|
| 6.3.1 | <i>I-V</i> characteristics..... | 66 |
| 6.3.2 | Intrinsic photocurrent spectra of ZnTe/ <i>n</i> -GaAs heterostructures | 67 |
| 6.3.3 | Photonic Zn and Te doping in GaAs by PLD | 69 |
| 6.3.4 | Bias dependence of the responsivity of ZnTe/ <i>n</i> -GaAs | 70 |
| 6.4 | Conclusions | 72 |
| 7 | SUMMARY | 73 |
| 8 | APPENDIX..... | 75 |
| 8.1 | Publications and patent list..... | 75 |
| 8.2 | Materials and equipment used in the experiment..... | 76 |
| 8.2.1 | Materials | 76 |
| 8.2.2 | Equipment list..... | 76 |
| 8.3 | Bibliography..... | 79 |
| 8.4 | References | 80 |

LIST OF FIGURES

| | |
|---|----|
| Figure 2.1: Energy band diagrams of (a) insulator, (b) semiconductor, and (c) metal | 6 |
| Figure 2.2: Schematic comparison of the spectral shapes of the photoconductivity | 8 |
| Figure 2.3: Photocurrent spectra of CdS for different τ_{sr}/τ_{ph} ratios. Curve 1 refers to the state of no surface recombination ($\tau_{sr} \gg \tau_h$ i.e. $\tau_{sr}/\tau_h \rightarrow \infty$), curve 2 represents the case when the surface lifetime becomes equal to the bulk lifetime ($\tau_{sr} = \tau_h$), and curve 3 represents infinitely small surface lifetime i.e. higher bulk lifetime ($\tau_{sr} \ll \tau_h$, $\tau_{sr}/\tau_h \rightarrow 0$)..... | 10 |
| Figure 2.4: Schematic diagram of pulsed-laser deposition..... | 11 |
| Figure 3.1: Zincblende crystal structure for CdS, ZnTe, and GaAs | 18 |
| Figure 3.2: Structure of polyethylene terephthalate monomer | 19 |
| Figure 3.3: Pulsed-laser deposition setup at Bowling Green State University | 26 |
| Figure 3.4: Deposition rate of CdS at various translational positions of the lens. This figure shows that the distance between the lens and the target is the focal length when the lens is kept at 24.7 cm on the translational stage..... | 27 |
| Figure 3.5: Deposition rate of CdS at 532 nm versus fluences. Plasma is seen beyond 0.64 J/cm^2 , which indicates the ablation threshold fluence. The line is a guide for the eyes..... | 28 |
| Figure 3.6: Optical images of plasma plume at various fluences. The pictures were taken with FinePix F450 camera and 523 nm light is blocked using an interference filter. | 29 |
| Figure 3.7: A picture of CdS/Plastic device with Al contacts. Inset shows thin-film CdS script on plastic produced with pulsed-laser deposition. | 30 |
| Figure 4.1: Pictures of (a) thin-film CdS on plastic and (b) original plastic substrate. | 32 |
| Figure 4.2: AFM images of thin-film PLD CdS on plastic with (a) micrometer and (b) nanometer resolution..... | 34 |
| Figure 4.3: XRD diffraction scan of (a) CdS/plastic (b) Plastic (c) CdS target..... | 35 |
| Figure 4.4: EDAX results for (a) CdS/Plastic, (b) Plastic substrate, and (c) CdS target. The spectra show that plastic does not contain Cd and S signals. | 38 |
| Figure 4.5: Schematic diagram of the thickness distribution setup. | 39 |
| Figure 4.6: Thickness distribution of thin-film CdS on plastic prepared with PLD at (a) 0.68 J/cm^2 (b) 3.31 J/cm^2 along major and minor axis. | 40 |
| Figure 4.7: Schematic diagram of DPC measurements. | 42 |

| | |
|--|----|
| Figure 4.8: The responsivity and PC spectra of Si photodiode used for the PC correction..... | 42 |
| Figure 4.9: PC (a) PC spectrum of CdS single crystal and CdS/Plastic prepared with PLD (b) transmission spectrum of CdS/Plastic and the plastic substrate; the inset shows a comparison of the PC and transmission spectra of CdS/Plastic. | 44 |
| Figure 5.1: (a) Magnitude of PC due to primary illumination (I) and quenched PC due to additional IR illumination (II), (b) diagram indicating primary and secondary illumination measurement scheme, and (c) mechanism of the quenching of the PC using the band diagram, where VB and CB represents the valance band and conduction band, respectively. | 47 |
| Figure 5.2: (a) Schematic diagram of the APC control using blue light illumination and (b) the emission spectrum of the blue LED..... | 49 |
| Figure 5.3: APC measurement setup at BGSU. The left side in this figure shows in detail a chopper, a lens, and the sample used in the quenching experiment. | 49 |
| Figure 5.4: XRD scan of CdS film on glass used for the APC quenching measurements. | 50 |
| Figure 5.5: (a) Optical transmission spectrum of the thin-film CdS and (b) optical gap determination. | 51 |
| Figure 5.6: (a) Alternating responsivity spectra of a thin-film CdS on the glass at different optical chopper frequencies at 100 V/cm. The inset shows responsivity versus chopper frequency plot at 2.6 eV. (b) Decay of the excited state CdS film on glass. The sample was excited with a blue argon ion laser. | 53 |
| Figure 5.7: (a) Alternating responsivity spectra at various biases and (b) corresponding responsivity plot versus bias at 2.6 eV..... | 54 |
| Figure 5.8: Quenching of AR at 10 V and 20 V due to additional constant blue LED illumination. | 55 |
| Figure 5.9: AR of CdS/glass at 20 V at (a) various excitation intensities from the monochromator at 488 nm when the blue LED is off, and (b) AR versus various quenching intensities from the blue LED at constant monochromatic chopped excitation at 488 nm. | 57 |
| Figure 5.10: DR/AR versus biases under constant monochromatic illumination at 516 nm when blue LED is on/off. Here DR and AR correspond to the DPC and APC, respectively. | 58 |
| Figure 5.11: Proposed mechanism of APC quenching by blue light..... | 59 |
| Figure 6.1: <i>I</i> - <i>V</i> measurement setup..... | 65 |
| Figure 6.2: Schematic diagram of the alternating photocurrent measurements..... | 65 |

Figure 6.3: Dark I - V characteristics of the ZnTe/ n -GaAs and n -GaAs samples. Here Al (+) and Al (-) polarity means top ZnTe film is connected with the positive and negative terminals of the power supply via the Al electrode. n -GaAs also has the same polarity configuration. 66

Figure 6.4: Intrinsic APC spectra of (a) ZnTe/ n -GaAs and (b) n -GaAs devices at different optical chopper frequencies. 68

Figure 6.5: Band structure modification of GaAs due to doping of Zn and Te atoms. 70

Figure 6.6: APC spectra at 650 Hz of (a) ZnTe/ n -GaAs and (b) n -type GaAs at different biases. Definition of bias polarity is identical with figure 6.3. 71

LIST OF TABLES

| | |
|---|----|
| Table 3.1: Publication list of pulsed-laser deposition of CdS..... | 21 |
| Table 3.2: Publication list of PLD of different materials on polymer substrates | 23 |
| Table 3.3: Thin-film CdS samples preparation parameters | 30 |
| Table 4.1: Composition of CdS thin films on plastic by EPMA | 37 |
| Table 6.1: Publication list of ZnTe/GaAs heterostructures | 62 |
| Table 8.1: Physical properties of CdS, ZnTe, and GaAs.” | 77 |
| Table 8.2: Cadmium sulfide X-ray diffraction data..... | 78 |